



### 800V N-Channel MOSFET

800 V

Voltage

#### Features

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V,I<sub>D</sub>@ 3.5A<1.55Ω
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.

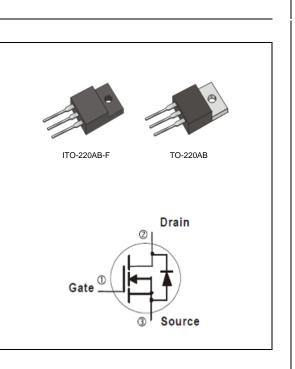
Current

7 A

• Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

- Case: TO-220AB, ITO-220AB-F Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- TO-220AB Approx. Weight : 0.067 ounces, 1.89 grams
- ITO-220AB-F Approx. Weight : 0.068 ounces, 2 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	TO-220AB	ITO-220AB-F	UNITS
Drain-Source Voltage		V <sub>DS</sub>	800		V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 30		V
Continuous Drain Current		I <sub>D</sub>	7		А
Pulsed Drain Current		I <sub>DM</sub>	28		А
Single Pulse Avalanche Energy (Note 1)		E <sub>AS</sub>	534		mJ
Power Dissipation	T <sub>c</sub> =25°C		154	50	W
	Derate above 25°C	PD	1.23	0.4	W/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150		°C
Typical Thermal resistance					
- Junction to Case		$R_{ extsf{ heta}JC}$	0.81	2.5	°C/W
- Junction to Ambient		$R_{ extsf{ heta}JA}$	62.5	120	





### **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static				1	ı	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	800	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V <sub>GS</sub> =10V,I <sub>D</sub> =3.5A	-	1.39	1.55	Ω
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =800V,V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 30V,V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =7A,V <sub>GS</sub> =0V	-	0.87	1.4	V
Dynamic (Note 4)						
Total Gate Charge	Qg		-	23	-	nC
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =640V, I <sub>D</sub> =7A, V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	7	-	
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =10V	-	9	-	
Input Capacitance	Ciss	Ciss V 25V V OV		1082	-	pF
Output Capacitance	$\frac{V_{DS}=25V, V_{GS}=0V,}{f=1.0MHZ}$		-	128	-	
Reverse Transfer Capacitance	Crss		-	6	-	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =400V, I <sub>D</sub> =7A,	-	34	-	
Turn-On Rise Time	t <sub>r</sub>	R <sub>G</sub> =25Ω	-	72	-	
Turn-Off Delay Time	td <sub>(off)</sub>	(Note 2,3)	-	63	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	35	-	
Drain-Source Diode				_		_
Maximum Continuous Drain-Source			-	-	7	A
Diode Forward Current	I <sub>S</sub>					
Maximum Pulsed Drain-Source			-	-	28	A
Diode Forward Current						
Reverse Recovery Time	trr	V <sub>GS</sub> =0V, I <sub>S</sub> =7A	-	590	-	ns
Reverse Recovery Charge	Qrr	dI <sub>F</sub> / dt=100A/us <sup>(Note 2)</sup>	-	4	-	uC

NOTES :

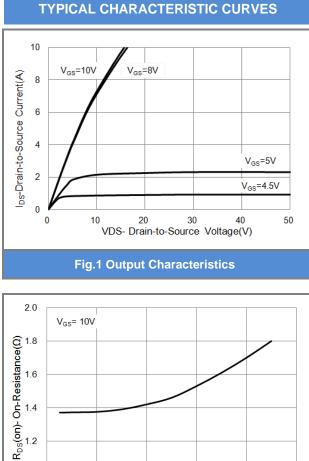
1. L=30mH,  $I_{AS}$ =5.85A,  $V_{DD}$ =50V,  $R_{G}$ =20 ohm, Starting  $T_{J}$ =25°C

2. Pulse width

3. Essentially independent of operating temperature typical characteristics.

4. Guaranteed by design, not subject to production testing





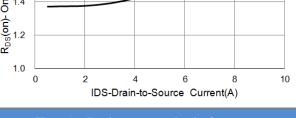
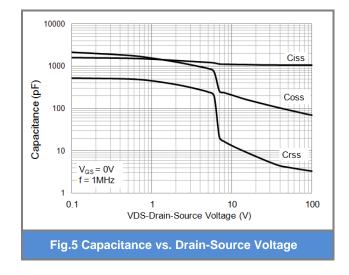
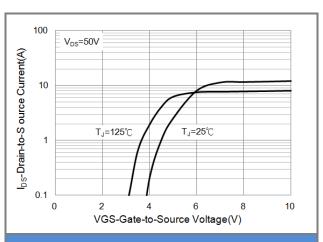


Fig.3 On-Resistance vs. Drain Current





**Fig.2 Transfer Characteristics** 

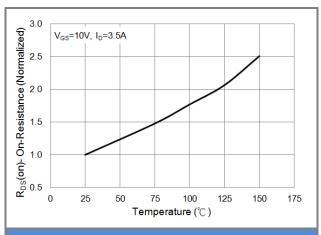
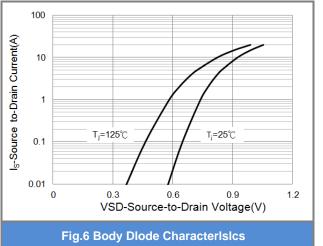


Fig.4 On-Resistsnce vs. Junction temperature





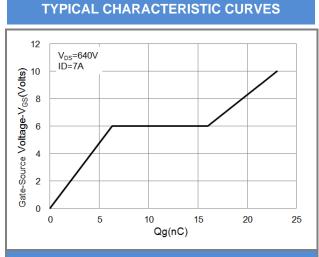
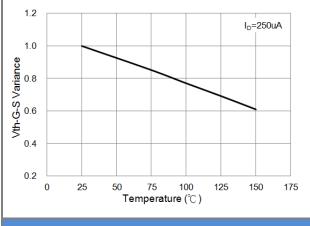
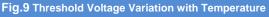
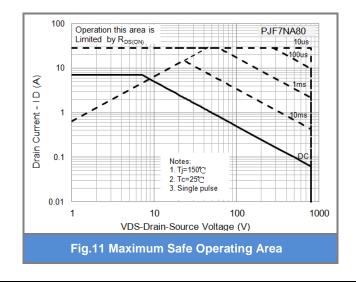
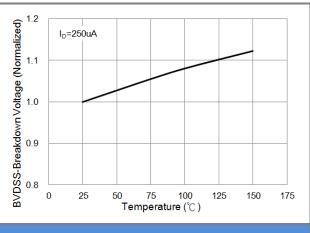


Fig.7 Gate-Charge Characteristics











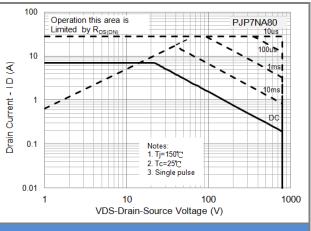
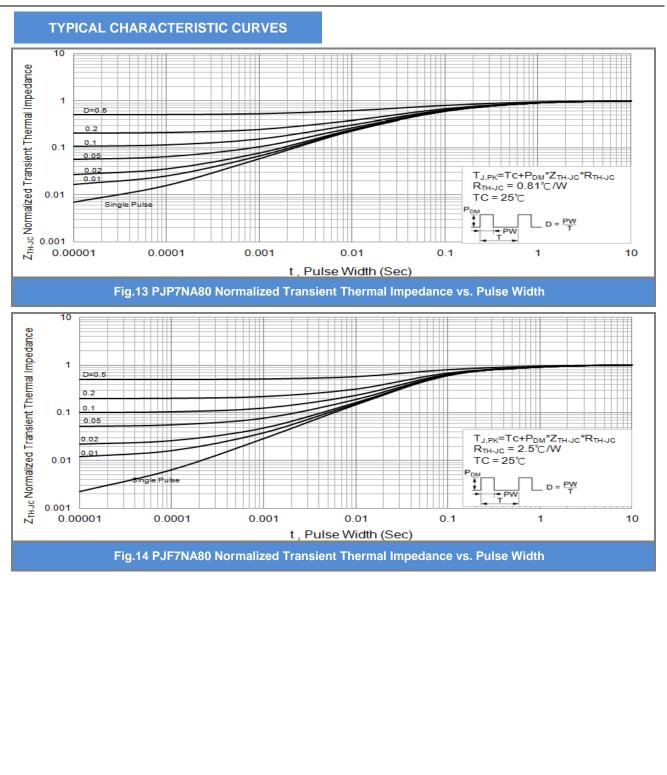


Fig.10 Maximum Safe Operating Area



-25

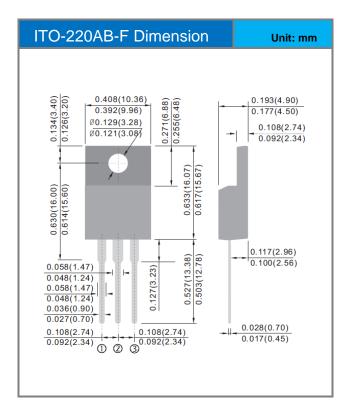
# PJP7NA80 / PJF7NA80

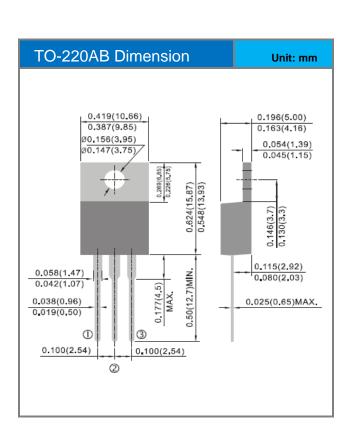






#### **Packaging Information**









### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJP7NA80_T0_00001	TO-220AB	50pcs / Tube	P7NA80	Halogen free
PJF7NA80_T0_00001	ITO-220AB-F	50pcs / Tube	F7NA80	Halogen free



### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.